

Title (en)

Method for producing a semiconductor-molding tablet

Title (de)

Verfahren zur Herstellung eines Harzverkapselungsscheibchens für Halbleiter

Title (fr)

Procédé pour produire une tablette de résine de scellement pour semi-conducteurs

Publication

EP 1498244 B1 20061004 (EN)

Application

EP 04016747 A 20040715

Priority

JP 2003198550 A 20030717

Abstract (en)

[origin: EP1498244A1] A method for producing a semiconductor-molding tablet, which can reduce formation of voids in the package due to increased density of the tablet. The method comprises a step of kneading an epoxy resin composition comprising components (A) an epoxy resin, (B) a phenol resin, and (C) an inorganic filler as essential components, a step of roll-molding the resulting kneaded composition into a sheet shape having a sheet density ratio of 98% or more, a step of pulverizing the resulting sheet-shaped compact, and a step of forming the pulverized material into a tablet shape having a tablet density ratio of 94% or more and less than 98%.

IPC 8 full level

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CPC (source: EP KR US)

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